









CEB13N10

100V **Δ** 140mΩ **Δ** 12.8A **Δ** Si MOSFET

SILICON Si MOSFET ▲ SMD type

N-channel enhancement mode

UL94V-0 rated flame retardant epoxy

TO263 (D2PAK) package ▲ MSL 3

Super high dense cell density for extremely low R_{DS(ON)}

High power and current handling capability

MAXIMUM RATINGS

Parameter (T _c = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V _{DS}	100V
Gate-Source Voltage	V _{GS}	±20V
Continuous Drain Current at T _C = 25°C	I _D	12.8A
Pulsed Drain Current Note 1	I _{DM}	50A
Maximum Power Dissipation at T _C = 25°C	P _D	65W
Power Dissipation Derating above 25°C	ΔP _D	0.43W/°C
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +175°C

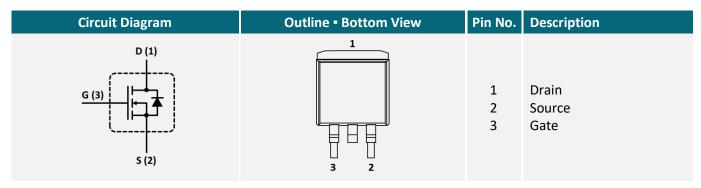
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R _{TH_JC}	2.3°C/W
Thermal Resistance, Junction-to-Ambient Note 2	R _{TH_JA}	62.5°C/W

APPLICATIONS

Battery Management Systems	E-Bike	Industrial Control	Power Inverter	UPS
+4-	50			5

PIN DESCRIPTION





ELECTRICAL CHARACTERISTICS \blacktriangle T_C = 25°C, unless otherwise noted

ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV_{DSS}	100			V
Zero Gate Voltage Drain Current	$V_{DS} = 100V, V_{GS} = 0V$	I _{DSS}			1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I_{GSSF}			100	nA
Gate Body Leakage Current, Reverse	V_{GS} = -20V, V_{DS} = 0V	I_{GSSR}			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_{D} = 250 \mu A$	$V_{GS(th)}$	2		4	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 6A$	R _{DS(ON)}		140	180	mΩ
Forward Transconductance	$V_{DS} = 10V, I_{D} = 6A$	g FS		5		S
Dynamic Characteristics Note 3						
Input Capacitance	$V_{DD} = 25V$, $V_{GS} = 0V$, $f = 1MHz$	C _{ISS}		295		pF
Output Capacitance	$V_{DS} = 25V$, $V_{GS} = 0V$, $f = 1MHz$	Coss	Coss			pF
Reverse Transfer Capacitance	$V_{DS} = 25V$, $V_{GS} = 0V$, $f = 1MHz$	C_{RSS}		35		pF
Switching Characteristics Note 3						
Turn-On Delay Time	V_{DD} = 80V, V_{GS} = 10V, I_{D} = 12.8A, $R_{G(ext)}$ = 9.1 Ω	t _{D(ON)}		10	20	ns
Turn-On Rise Time	V_{DD} = 80V, V_{GS} = 10V, I_{D} = 12.8A, $R_{G(ext)}$ = 9.1 Ω	t _R		8	16	ns
Turn-Off Delay Time	V_{DD} = 80V, V_{GS} = 10V, I_{D} = 12.8A, $R_{G(ext)}$ = 9.1 Ω	t _{D(OFF)}		17	35	ns
Turn-Off Fall Time	$V_{DD} = 80V$, $V_{GS} = 10V$, $I_{D} = 12.8A$, $R_{G(ext)} = 9.1\Omega$	t _F		8	16	ns
Total Gate Charge	$V_{DD} = 80V$, $V_{GS} = 10V$, $I_D = 12.8A$	Q_{G}		12	16	nC
Gate Source Charge	$V_{DD} = 80V$, $V_{GS} = 10V$, $I_D = 12.8A$	Q_{GS}		3.3		nC
Gate Drain Charge	V_{DD} = 80V, V_{GS} = 10V, I_D = 12.8A	Q_{GD}		5.3		nC
Drain-Source Diode Characteristics ar	nd Maximum Ratings					
Drain-Source Diode Forward Current		Is			12.8	Α
Drain-Source Diode Forward Voltage Note 2	V _{GS} = 0V, I _S = 12.8A	V_{SD}			1.5	V

Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 3: Guaranteed by design, not subject to production testing.



REFERENCE DATA A TYPICAL DEVICE PERFORMANCE



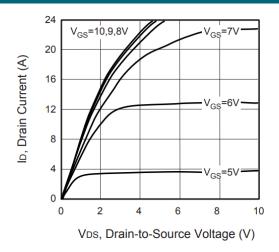
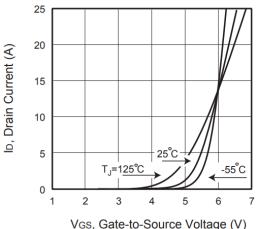


Fig. 2 • Transfer Characteristics



Vgs, Gate-to-Source Voltage (V)

Fig. 3 • Capacitance

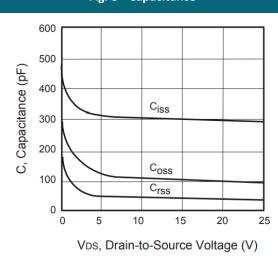


Fig. 4 • On-Resistance Variation with Temperature

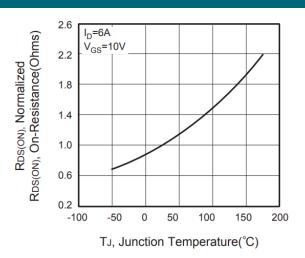


Fig. 5 • Gate Threshold Variation with Temperature

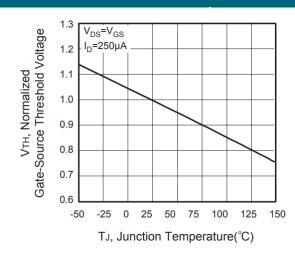
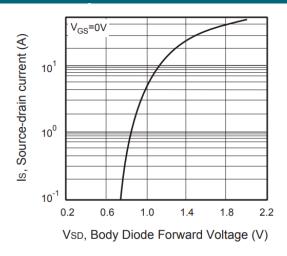


Fig. 6 - Body Diode Forward Voltage Variation with Source Current



MGT ▲ Manufacturer Group of Technology



REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

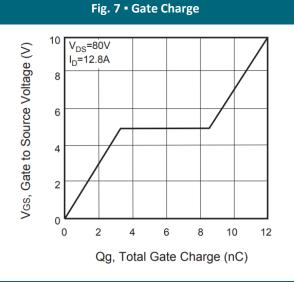


Fig. 8 • Maximum Safe Operating Area

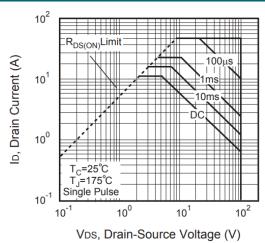
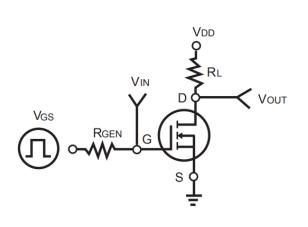


Fig. 9 • Switching Test Circuit

Fig. 10 • Switching Waveforms



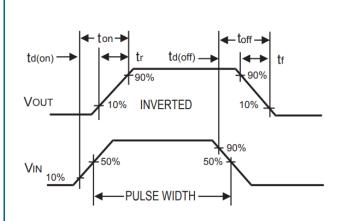
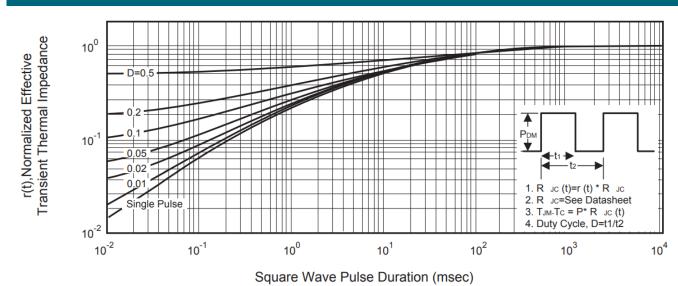


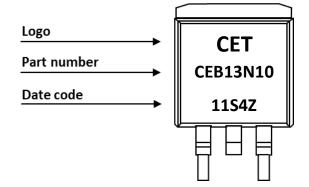
Fig. 11 • Switching Test Circuit



MGT ▲ Manufacturer Group of Technology

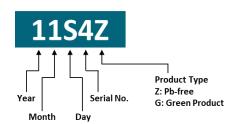


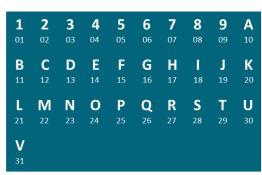
PART MARKING



DATE CODE

Example: 11S4Z



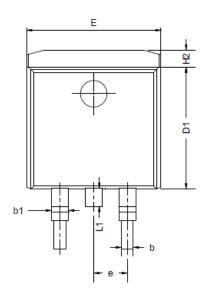


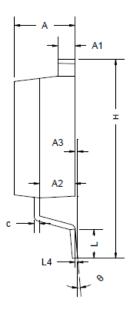
Coding list for "Day"

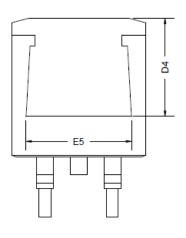


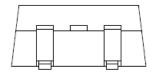


PACKAGE OUTLINE









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	
Α	4.37	4.57	4.77	
A1	1.22	1.27	1.42	
A2	2.49	2.69	2.89	
A3	0.00	0.13	0.25	
b	0.70	0.81	0.96	
b1	1.17	1.27	1.47	
С	0.30	0.38	0.53	
D1	8.50	8.70	8.90	
D4	6.60	-	-	

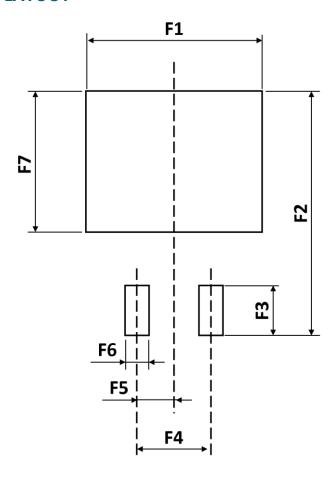
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)			
Е	9.86	10.16	10.36			
E5	7.06	-	-			
е	2.54 BSC					
Н	14.70	15.10	15.50			
H2	1.07	1.27	1.47			
L	2.00	2.30	2.60			
L1	1.40	1.55	1.70			
L4	0.25 BSC					
θ	0°	5°	9°			

ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.	
CEB13N10	TO263 (D2PAK)	Reel	800pcs	800pcs	6,400pcs	



RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	
F1	-	12.20	-	
F2	-	16.90	-	
F3	-	2.54	-	
F4	-	5.08	-	

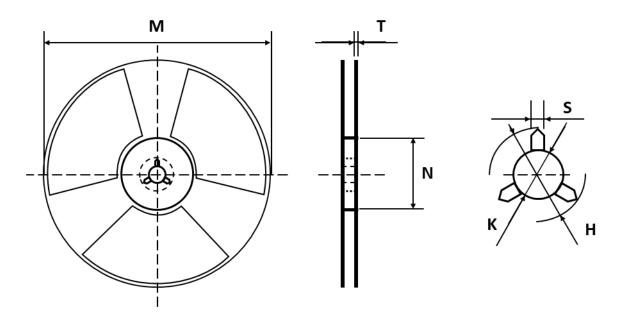
Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	
-	2.54	-	
-	1.60	-	
-	9.75	-	
	(Min.) - -	- 2.54 - 1.60	

Notes:

- 1. The suggested land pattern dimensions have been provided for reference only.
- 2. For further information, please reference document IPC-7351A.

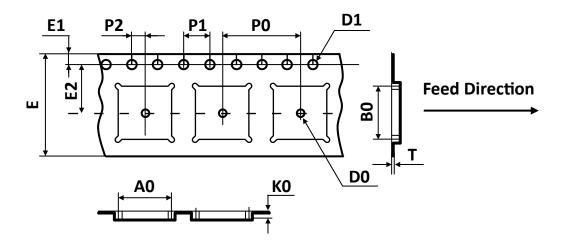


REEL DIMENSIONS ▲ All dimensions in mm



Tape Size	Reel Size	M	N	T	Н	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
24mm	Ø330	±2.00	±0.50	±0.20	±0.50	+0.50	+0.50
		12.00	±0.50	±0.20	±0.50	-0.20	-0.20

TAPE DIMENSIONS ▲ All dimensions in mm

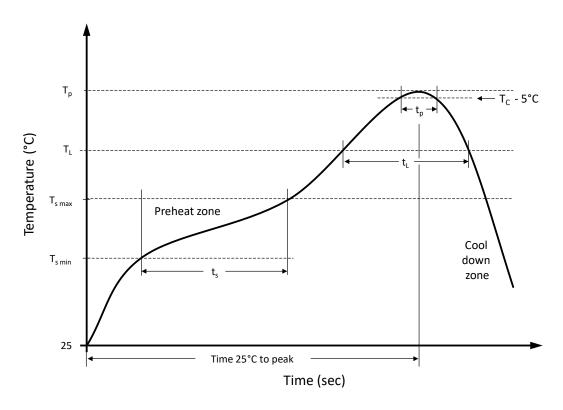


Pa	ckage	Α0	В0	КО	D0	D1	E	E1	E2	Р0	P1	P2	Т
TC	0263	10.80	16.30	4.85	1.50	1.55	24.00	1.75	11.50	16.00	4.00	2.00	0.35
(D ²	² PAK)	±0.10	±0.10	±0.10	±0.10	±0.05	±0.30	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05

Note: All dimensions meet EIA-481-D requirements.



RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T _{s max}	150 °C	200 °C
Preheat time t _s from T _{s min} to T _{s max}	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	T_L	183 °C	217 °C
Time t _L maintained above T _L	t _L	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T _L to T _p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

DISCLAIMER

Except for the written expressed warranties, MGT does not implicitly, by assumption or whatever else, warrant, under-take, promise any other warranty or guaranty for any MGT product.

All information and technical specifications made available by MGT are for guidance only and we reserve the right to change or modify them without prior notice. Unless expressly stated in writing by MGT, we reject any guarantees, obligations, or warranties.

All MGT products with the technical specifications described are suitable for use in certain applications. Operating, production, storage and environmental conditions can have a massive influence on the parameters mentioned in the data sheets, which cause the performance to vary over time.

It is subject to the user's duty of care to design and validate his products in such a way that appropriate measures are taken, such as protective circuits or redundant systems to ensure the safety standards required in the application.

MGT components are not designed or rated for use in life support, rescue, safety critical, military, or aerospace applications where failure or malfunction could result in property or environmental damage, serious injury or death. In the aforementioned cases, please contact us before using MGT products.

In principle, we reserve all rights and MGT's general terms and conditions apply. You can find them on our website www.mgt.co.com.